

EXL Recoil Detector Experience With the CHICSi Detector

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CHICSi detector system

UHV compatibility studies

CHICSi auxiliary detectors

Possible CHICSi detector array for EXL

CHIC Collaboration

Lund, Uppsala

Copenhagen, Dubna

St. Petersburg, Cracow

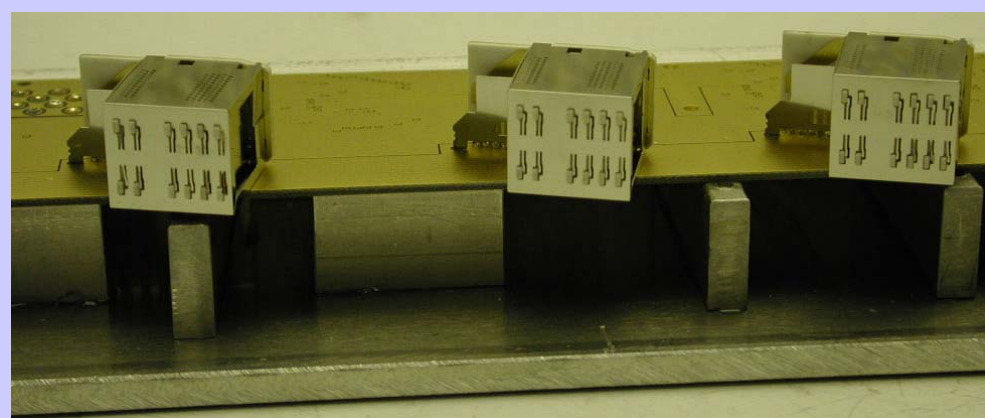
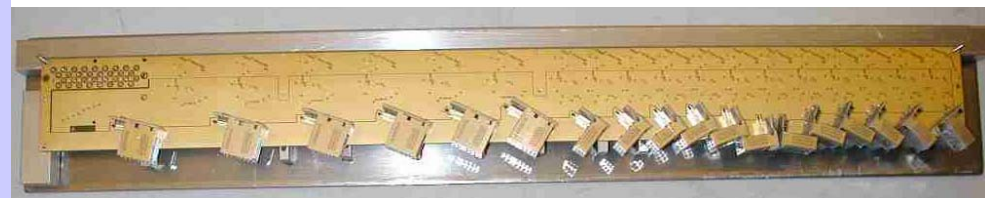
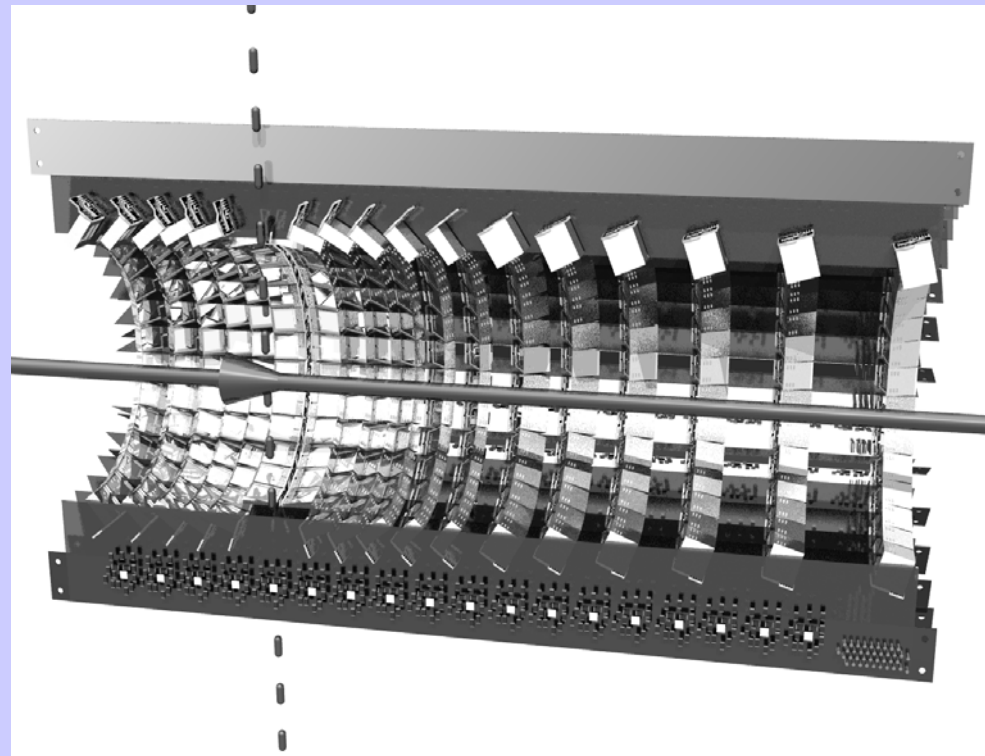
CHICSi: CELSIUS Heavy Ion Collaboration Silicon Detector System

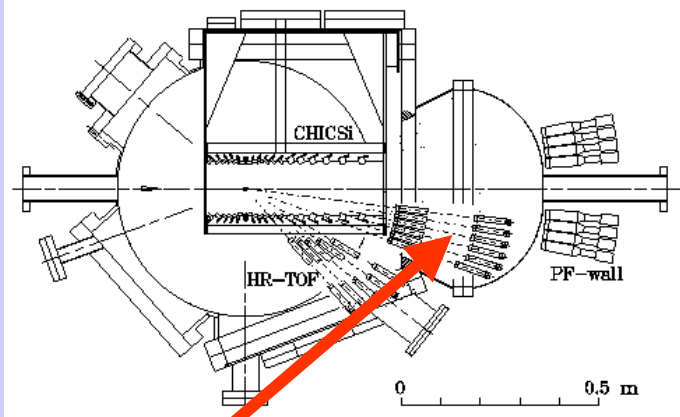
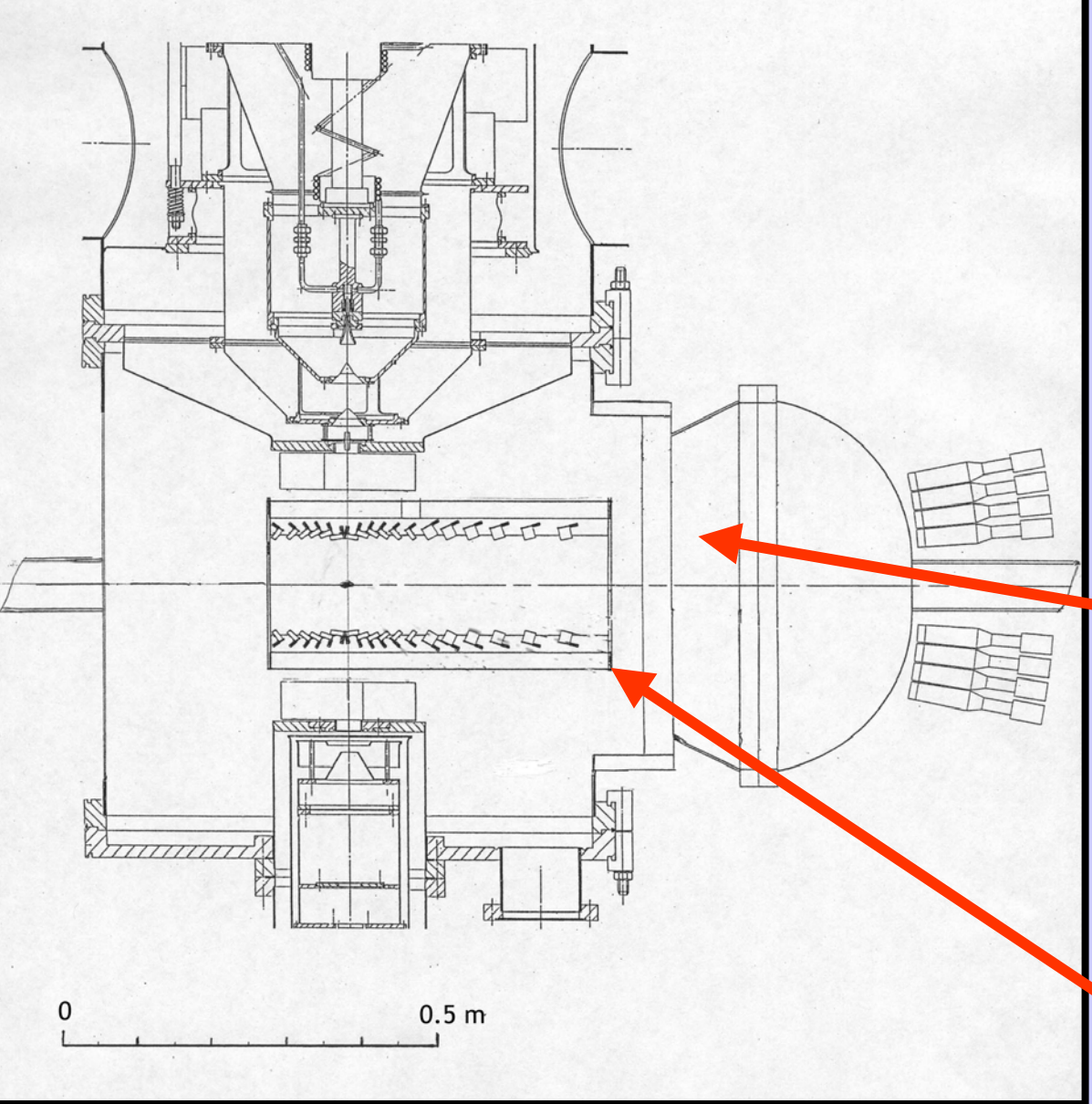
- A Compact Ultra-high Vacuum
Compatible Detector System for Studies
of Proton and Light Heavy-ion (N-Ar)
Reactions on Cluster-jet Targets of Ar -
Xe

- 504 1.0 Cm² Telescopes Si (10 μM) + Si
(300 μM) + Si (300 μM Veto) or

6 Mm GSO Crystal + PhD

-Identify Intermediate Mass Fragments $3 \leq Z \leq 10$; Threshold 700A keV

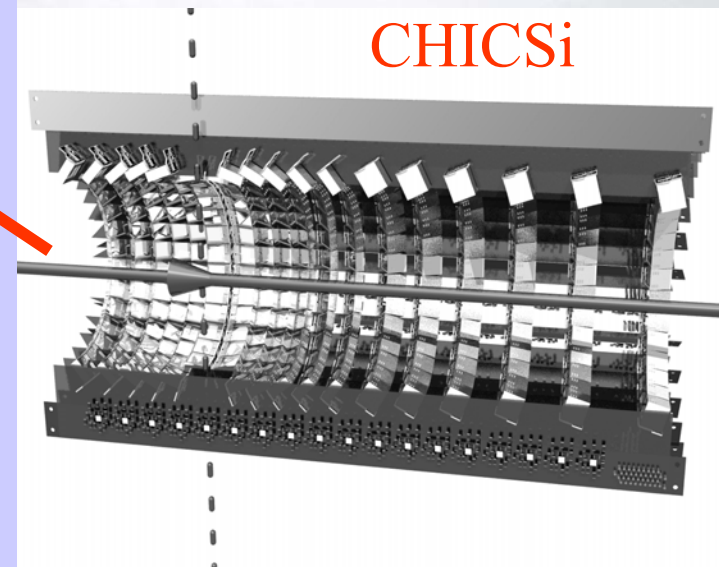




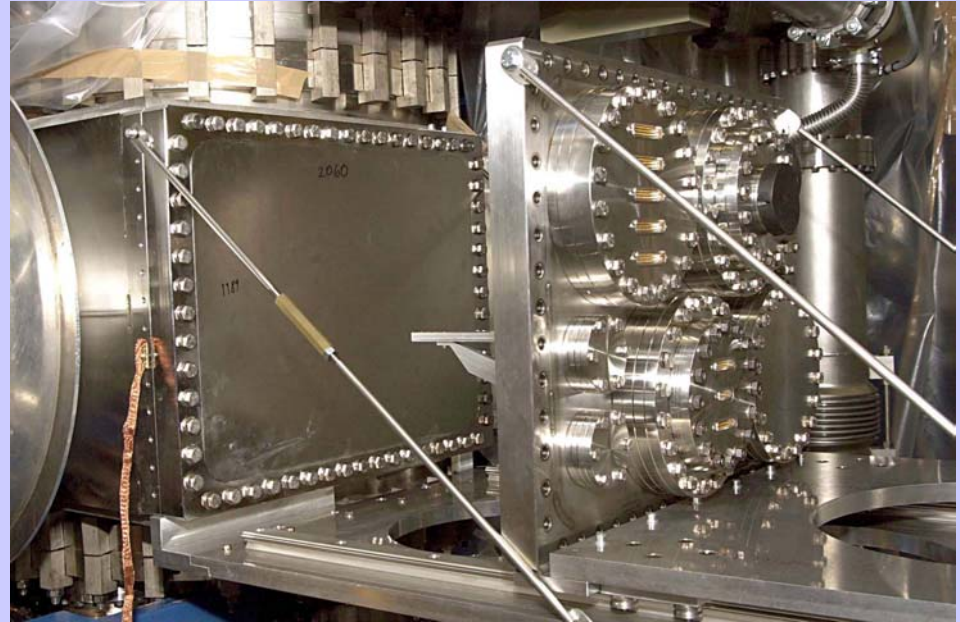
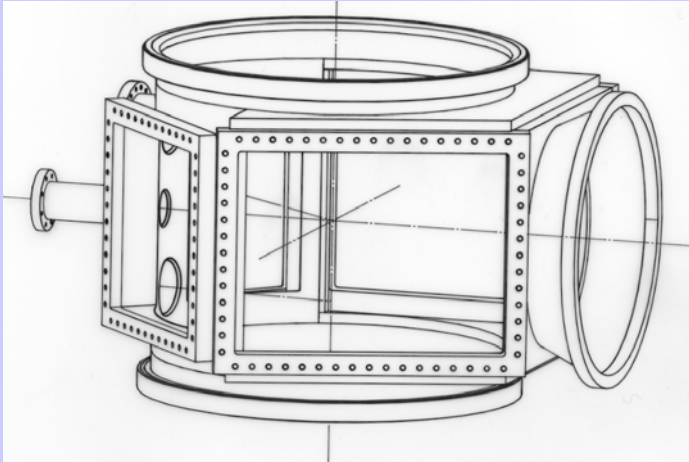
HR-TOF



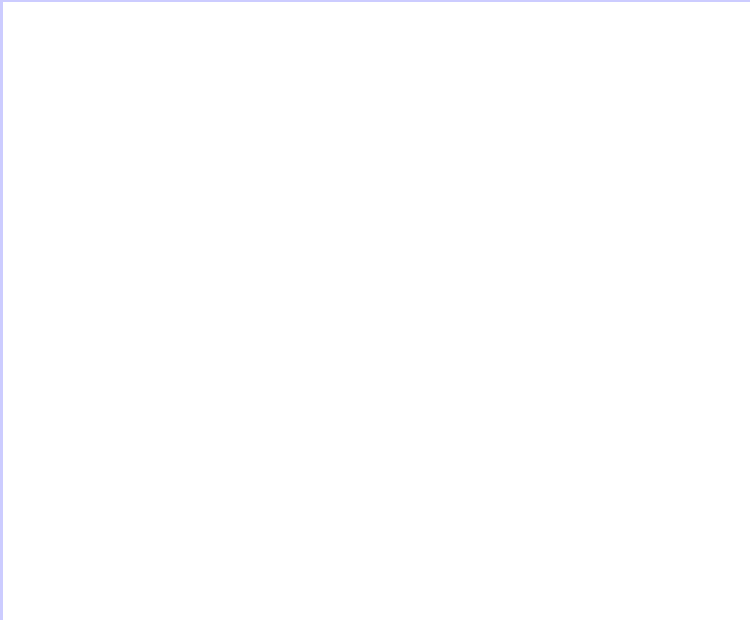
CHICSi



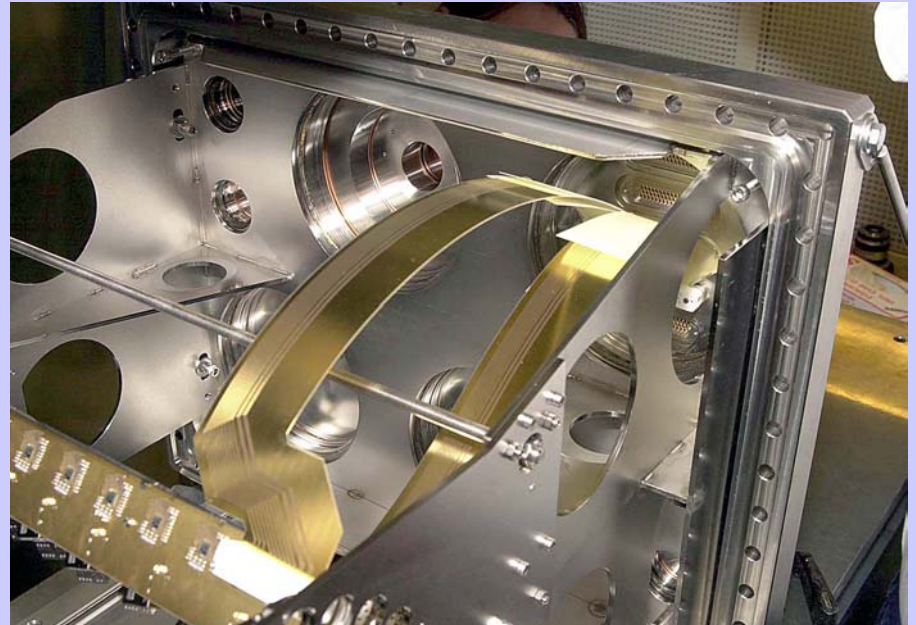
Scattering chamber



Readout cables
Kapton-insulated cables



Printed-circuit board cable



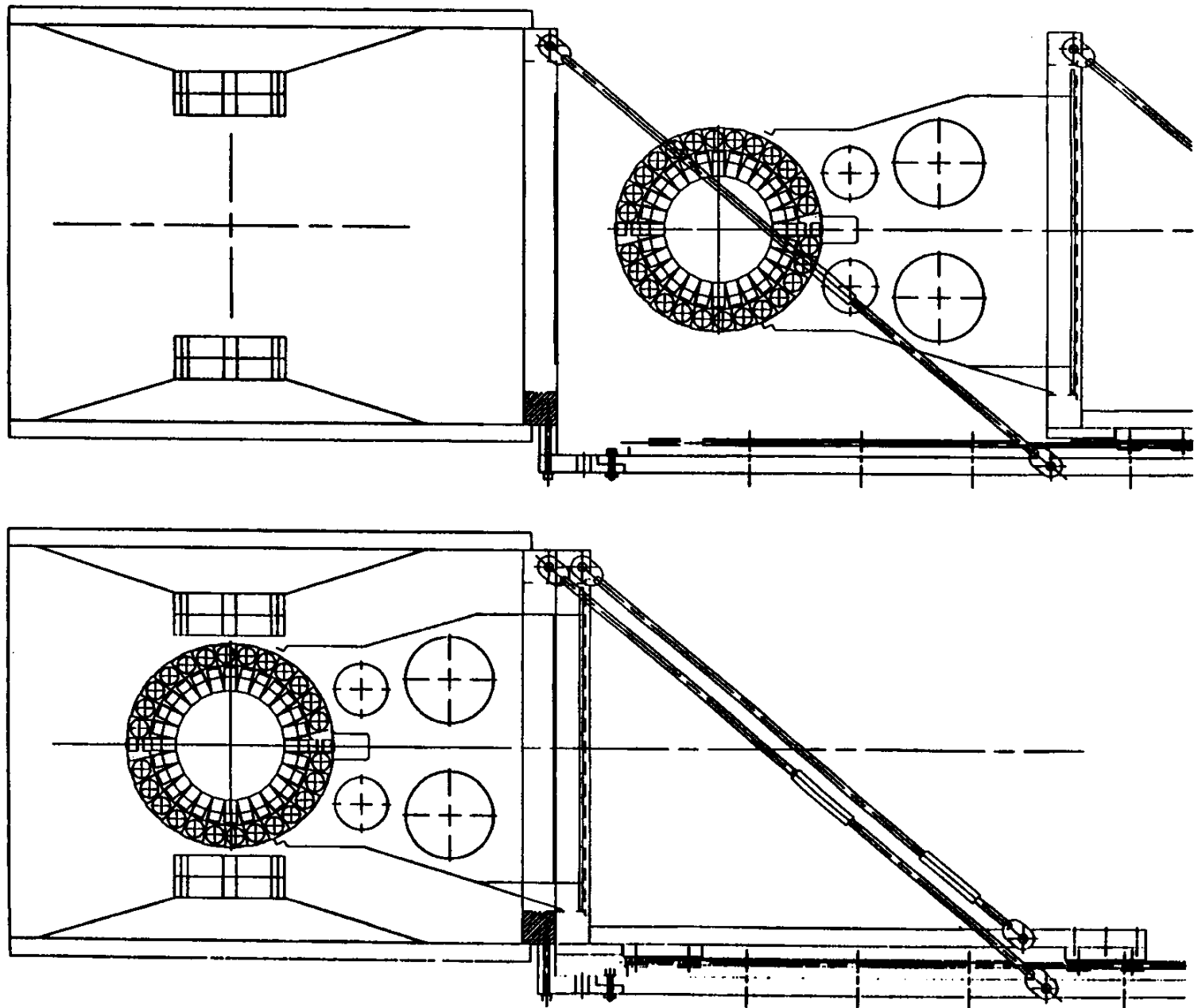


Fig. 5. A vertical plane cut of CHICSi and the scattering chamber. Upper: CHICSi located outside the chamber. Lower: CHICSi located in the chamber. The total (internal) height of the chamber is 456 mm.

UHV compatible Materials needed

- New type of rectangular flanges for large ports
- Printed circuit boards for
 - detector mounts
 - VLSI readout
- Coaxial cables
- Flat cables
- Contacts for cables and printed circuit boards
- Conducting and insulating two-component glues

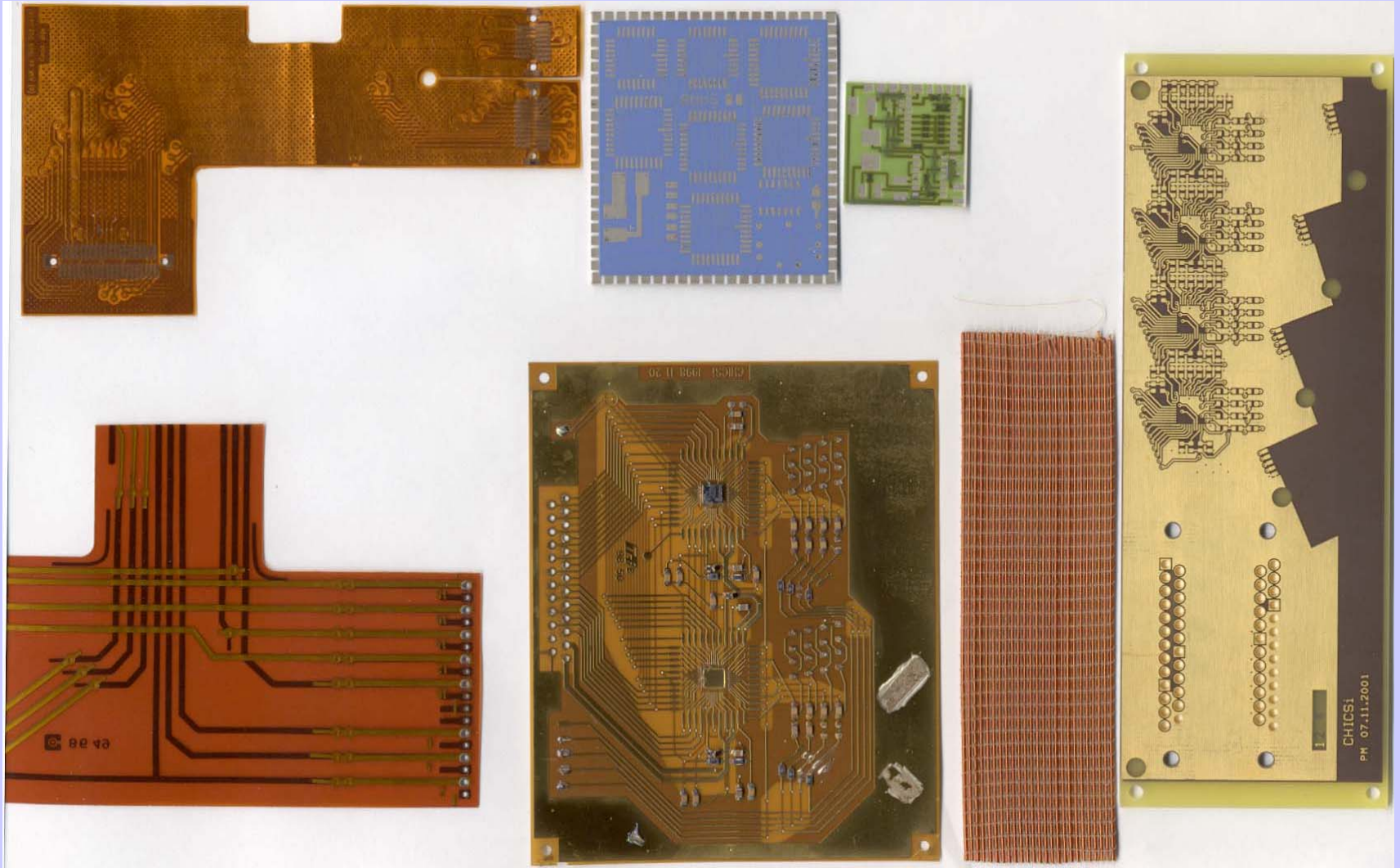
Insulators

Macor	Can break when machining Threads are fragile
Vespel	Varying outgassing Discharge can cause carbonizing
PEEK	High outgassing, H ₂ O
Photoveel	SiO ₂ , Al ₂ O ₃ ... Lower outgassing
M-soft Shapal	AlN Low outgassing, Expensive

Kapton

Ceramics

FR-4



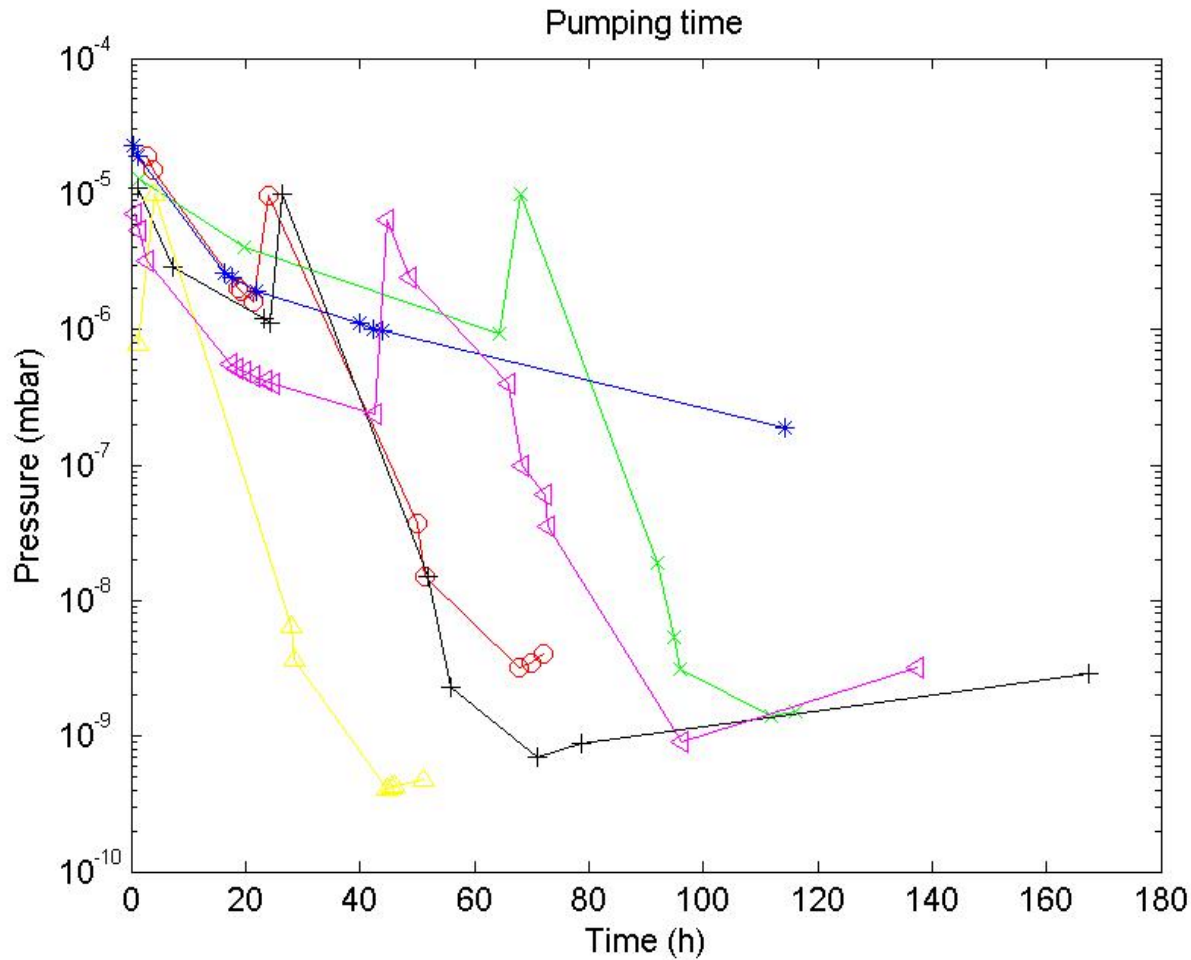
Outgassing measurements

Material	Area cm ²	Bake-out in air		Bake-out in vacuum		H ₂ W/m ²	H ₂ O W/m ²	CO W/m ²	Total outgassing rate W/m ²
		Tem p °C	Tim e h	Tem p °C	Time h				
PRINTED CIRCUIT BOARD MATERIALS									
Pyralux (2 layers)	19			150	20	2·10 ⁻⁵	4·10 ⁻⁷	3·10 ⁻⁶	3·10 ⁻⁵
AP (2 layers)	98			150	20	2·10 ⁻⁷	4·10 ⁻⁸	3·10 ⁻⁷	1·10 ⁻⁶
Epoxy-Acrylic (2 layers)	30			150	20	1·10 ⁻⁷	3·10 ⁻⁷	3·10 ⁻⁷	3·10 ⁻⁶
Epoxy-Glass fibre, 1 layer	36			150	20	4·10 ⁻⁷	4·10 ⁻⁸	4·10 ⁻⁸	2·10 ⁻⁶
Alumina (14 layer electrical print)	32			150	20				3·10 ⁻⁷
Glass reinforced Kapton™	74			150	24				2·10 ⁻⁸
FR4	475			150	30				1.5·10 ⁻⁸
FR4	331	150	24						6·10 ⁻⁷
FR4	331	150	24	150	23	2·10 ⁻¹⁰			6·10 ⁻⁸
FR4	331	150	24	150	77				4·10 ⁻⁹
FR4 – 6 layers	120			150	30	<1·10 ⁻⁷			5·10 ⁻⁷
INSULATORS									
PEEK				150	20	1.4·10 ⁻⁶	8·10 ⁻⁷	5·10 ⁻⁷	3·10 ⁻⁶
Photoveel	44			150	20	1.6·10 ⁻⁷	1.0·10 ⁻⁸	3·10 ⁻⁸	2·10 ⁻⁷
M-soft shapal	44			150	20	1.4·10 ⁻⁸	1.0·10 ⁻⁹	4·10 ⁻⁹	1·10 ⁻⁷
Macor™	75			200	26				4·10 ⁻⁸
Macor™, 30 min air expos	75								2·10 ⁻⁶

Outgassing measurements Epoxies (EPO-TEK)

Type	Weight	Bake-out in air		Bake-out in vacuum		H ₂	H ₂ O	CO	CO ₂	CH ₄	Total outgassing rate
		Temp (°C)	Time (h)	Temp (°C)	Time (h)						
377	1.15	90	1.5								$1.4 \cdot 10^{-7}$
377	1.15	90	1.5	150	24	$1.3 \cdot 10^{-10}$	$1.8 \cdot 10^{-11}$	$2.0 \cdot 10^{-11}$	$4 \cdot 10^{-12}$	$6 \cdot 10^{-12}$	$4 \cdot 10^{-10}$
H20 E	2.16	90	1.5			$4 \cdot 10^{-8}$	$1.6 \cdot 10^{-8}$	$6 \cdot 10^{-9}$	$8 \cdot 10^{-10}$		$6 \cdot 10^{-8}$
H20 E	2.16	90	1.5	150	24	$4 \cdot 10^{-11}$	$1.2 \cdot 10^{-10}$	$3 \cdot 10^{-11}$	$2 \cdot 10^{-11}$	$1.4 \cdot 10^{-11}$	$7 \cdot 10^{-10}$
H27 D	3.90	90	1.5								$1.1 \cdot 10^{-7}$
H27 D	3.90	90	1.5	150	24						$3 \cdot 10^{-8}$

Outgassing from cables



- Red o AMGAB cable
- Green x KAP2
- Blue * KAP2 airbaked inst. after 48h delay
- Black + KAP3
- Yellow ^ Empty
- Magenta < KAP2 airbaked inst. in chamber directly

HR-TOF time detector

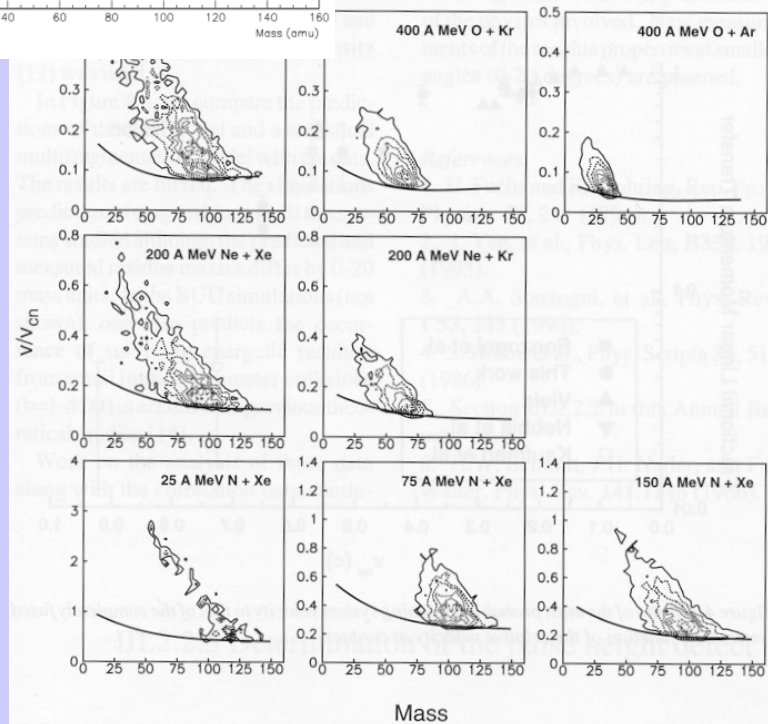
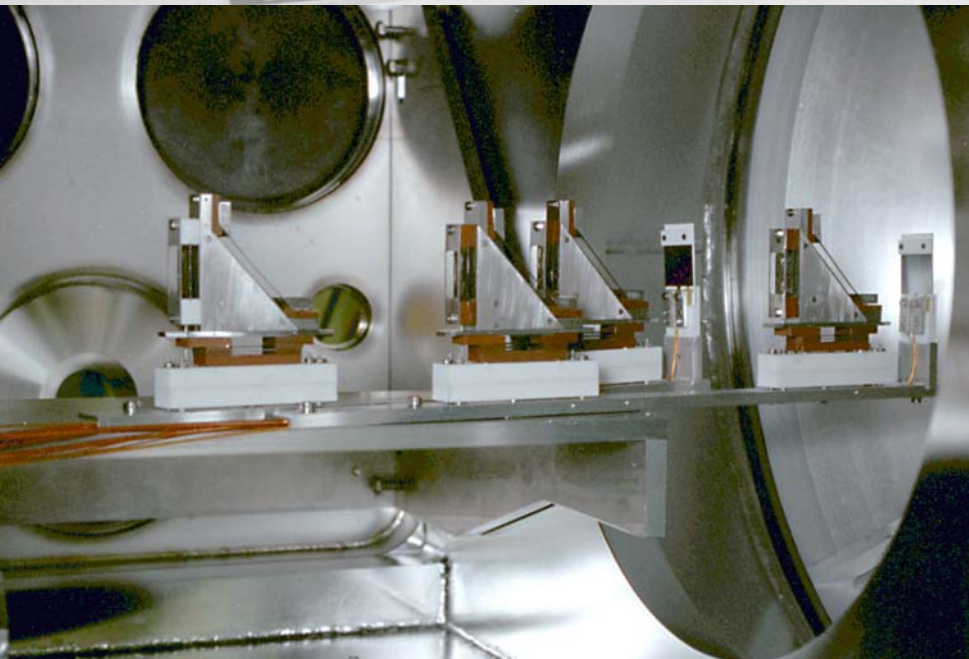
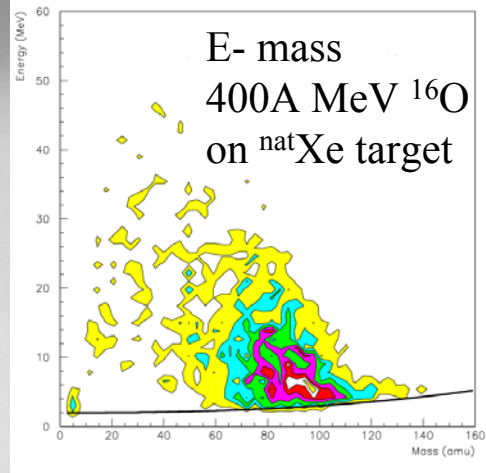
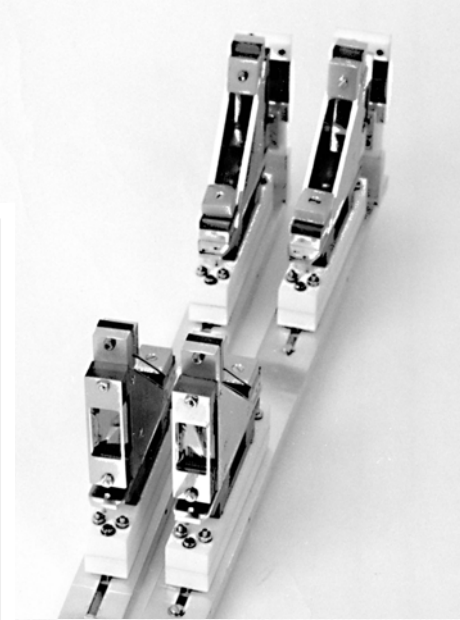
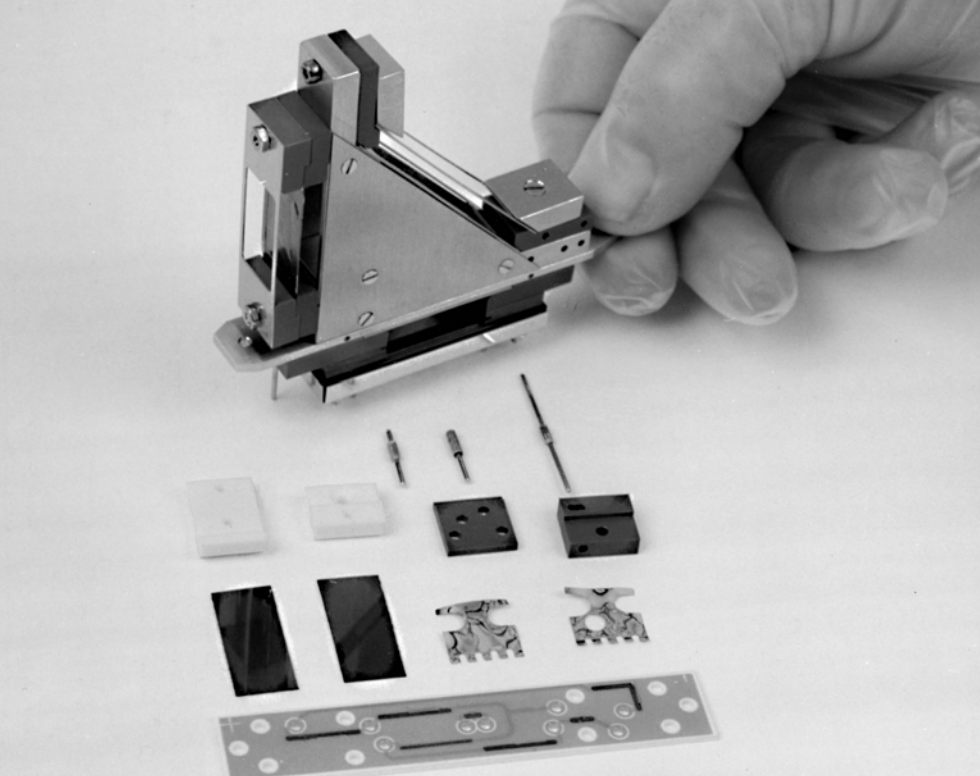


Figure 4.1. Dependence of the measured residue mass on the fragment velocity, expressed as a fraction of the compound nuclear velocity for the systems studied in this work

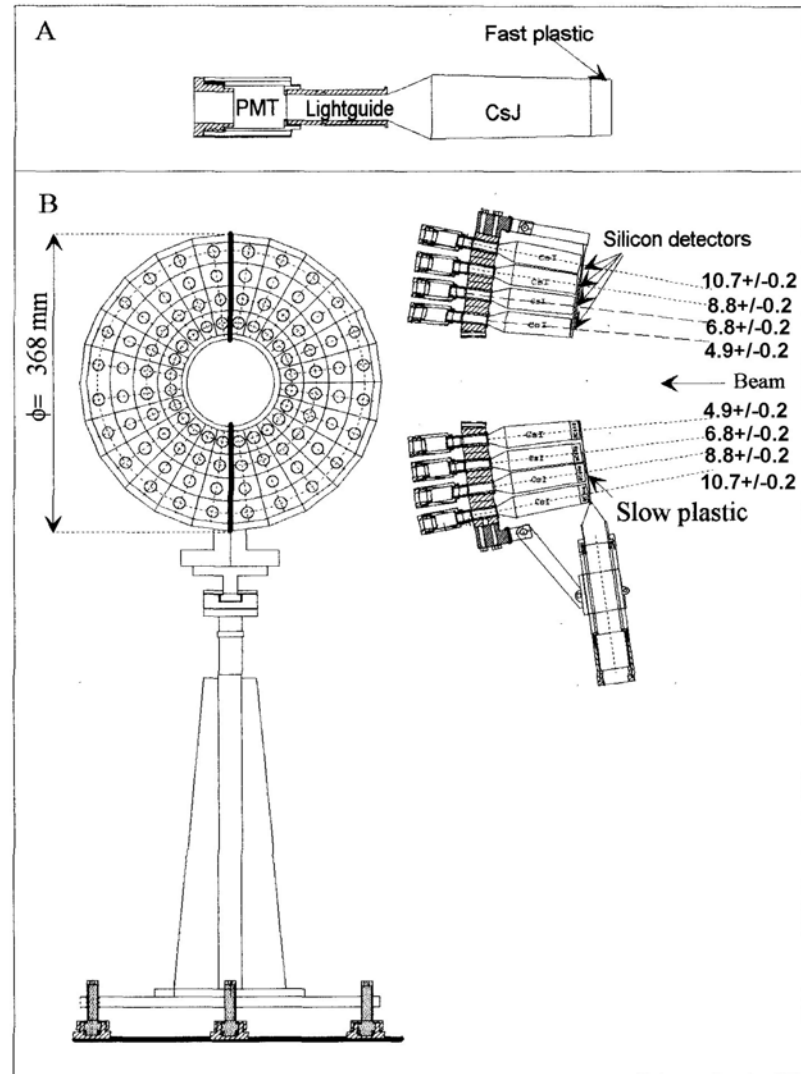
PF-WALL

Projectile Fragmentation
WALL

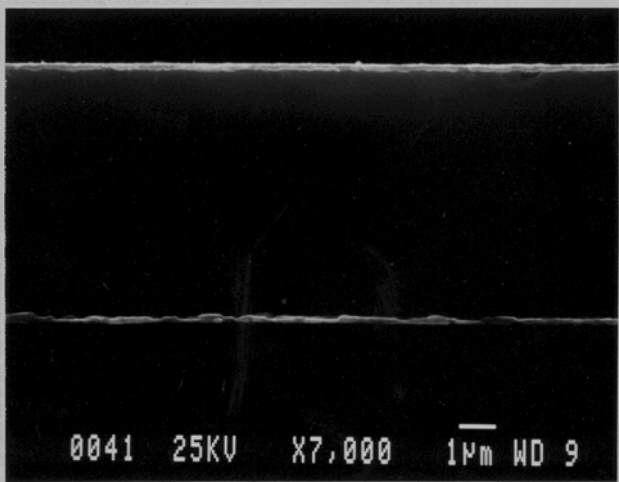
$3.9^\circ - 11.7^\circ$

Z identification: $Z \leq 18$,

Mass identification: H - He



Integrated ΔE -E detector



ΔE

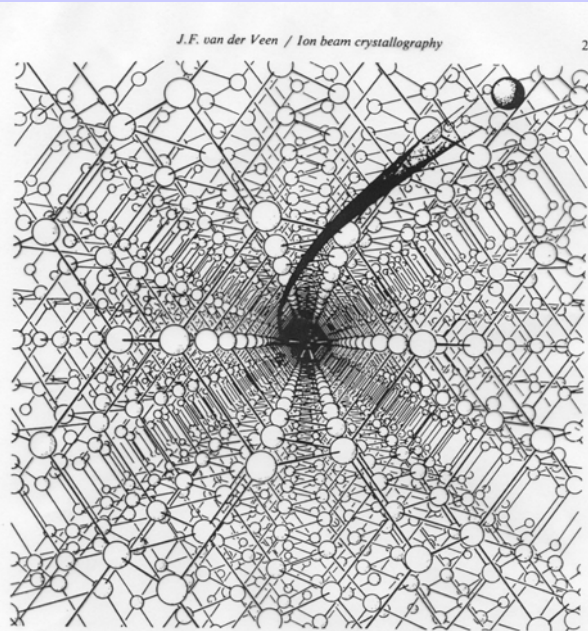
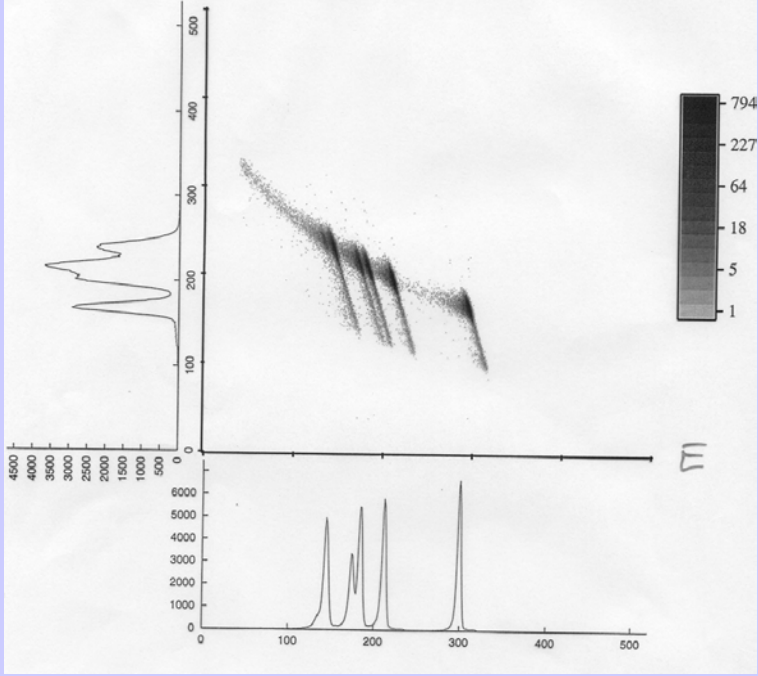
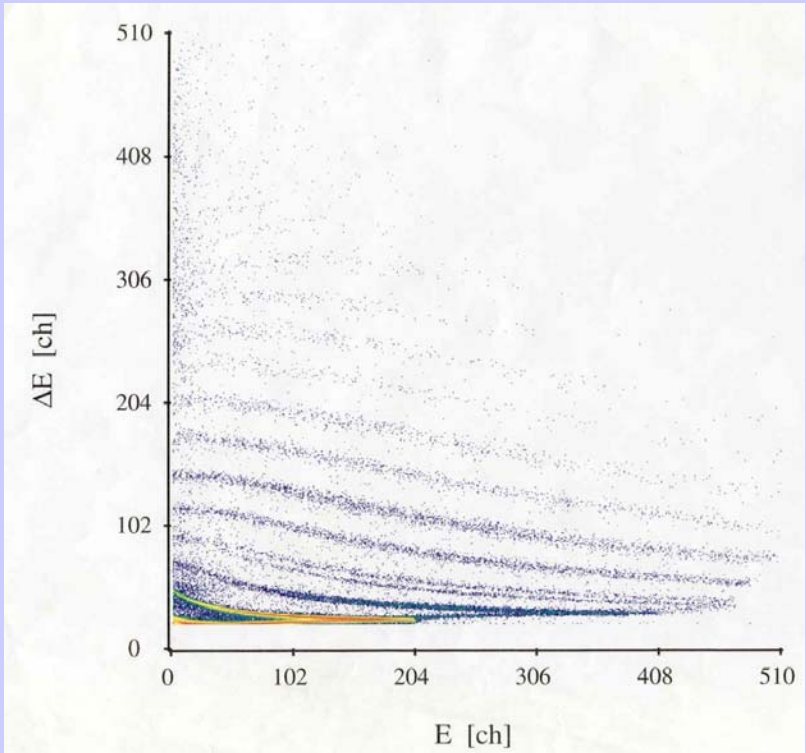


Fig. 9. Channeling of a particle in a crystal. From "Channeling in Crystals", by W. Brandt, Copyright © (March, 1968) by Scientific American, Inc., all rights reserved.

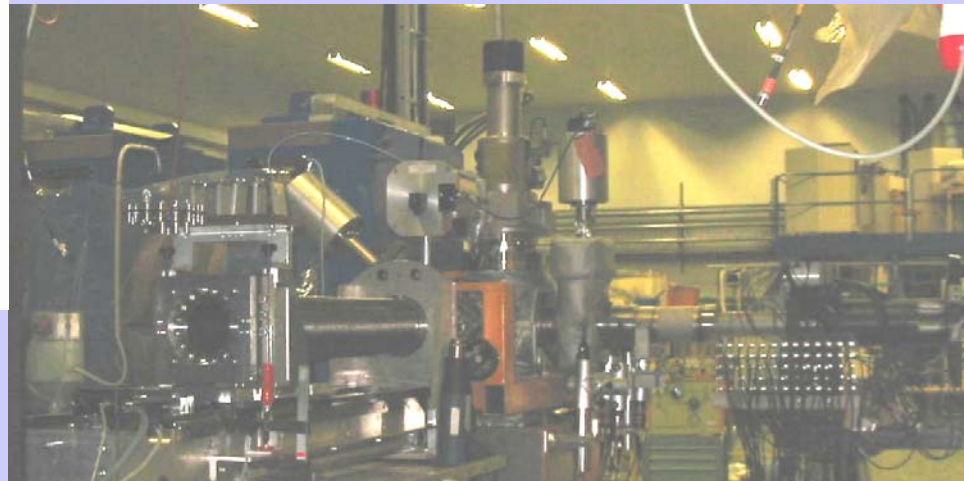
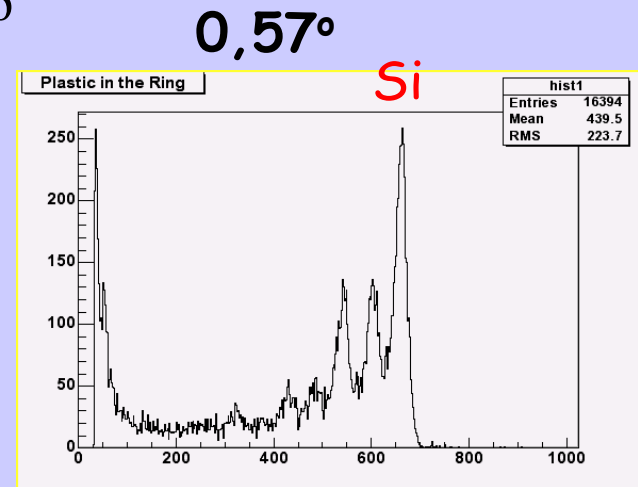
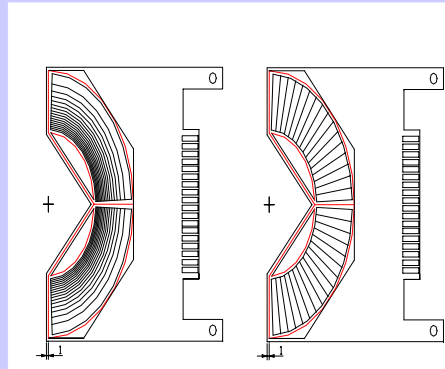
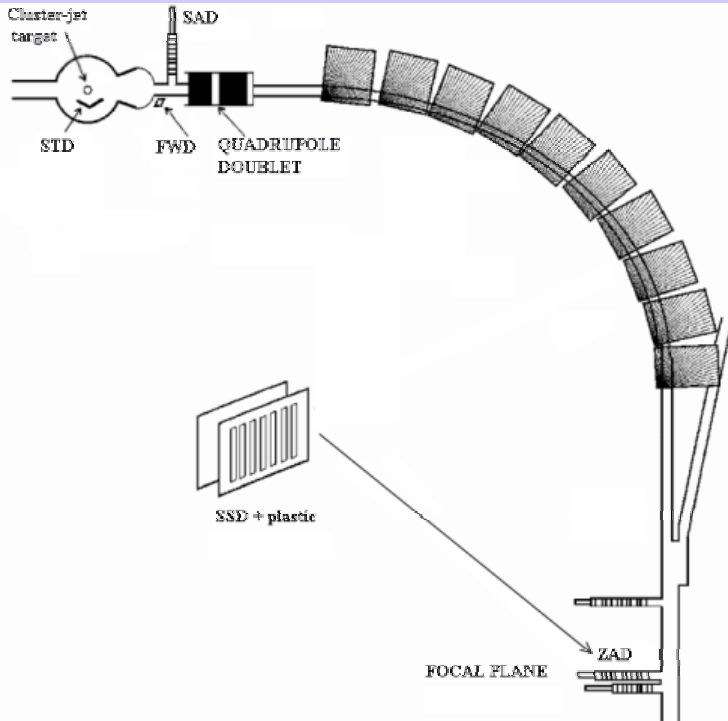


Small Angle Detector (SAD)

Study of Silicon SEU-hazardous recoils at CELSIUS

At 2300 cm distance from the H jet: 0.6° - 1.12°

SAD core element : custom-made 300 um Silicon Strip Detector



CHICSi experiments

Pion production

Slow ramping experiments

Isotope ratios

Isobar ratios

Ne+Ar 2003-2004

p + Ar, Kr, Xe Autumn 2004

Ne + Ar, Kr, Xe Spring 2005

Xe + Xe at ESR 2006?

Charge distribution of low energy fragments from the $^{20}\text{Ne} + ^{40}\text{Ar}$ reaction at 200A MeV. CHICSi data (Oct. 2003)

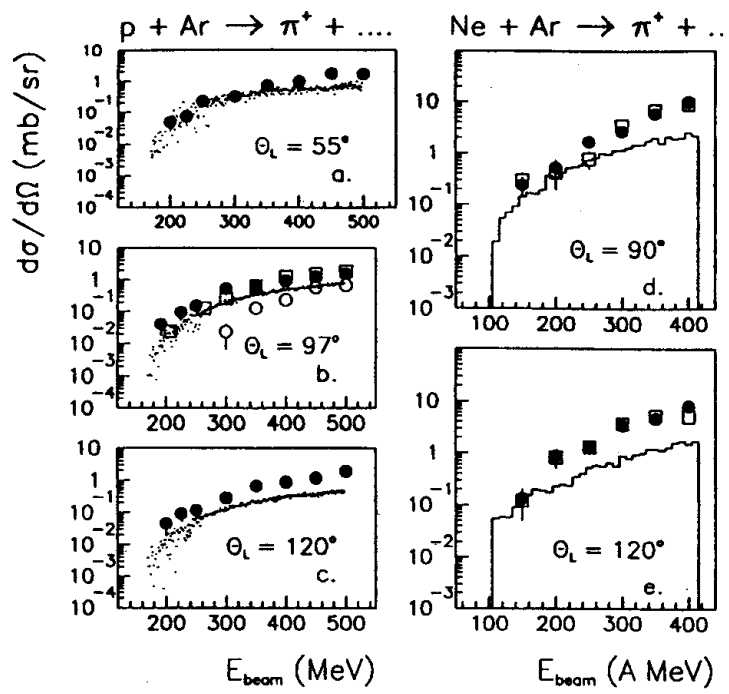
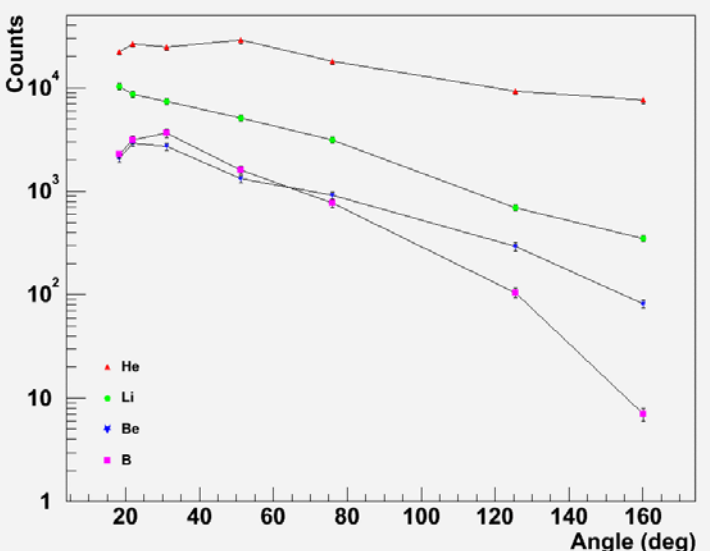


FIG. 2. Differential π^+ cross sections in $p + \text{Ar}$ collisions at three angles (55° , 97° , 120°), and in $\text{Ne} + \text{Ar}$ collisions at two angles (90° , 120°). The points represent BUU calculations

Angular distribution for He, Li, Be and B 1-7 A MeV



CHICSi and EXL

Arrange 8 – 12 GMB's in the angular region $20^\circ - 90^\circ$
each with (8 – 12) telescopes,
mounted as a semi-cylinder of radius ~ 30 cm.

In this way installation can be performed in the same way as
CHICSi at CELSIUS with all equipment on one flange.

Instead of using only two $300 \mu\text{m}$ Si detectors, as suggested for
EXL transfer reactions, we suggest to introduce (at least in one
part of the array) $15 \mu\text{m} + 300 \mu\text{m}$ Si + $6000 \mu\text{m}$ GSO/PD
detectors stopping protons from 1 to 60 MeV.

This is a reasonable choice for interferometry and could
possibly be used for other EXL (elastic?) reactions.

**The Svedberg-laboratoriet
Entré**

